CMLD2004G

SURFACE MOUNT SILICON DUAL, ISOLATED HIGH VOLTAGE SWITCHING DIODE



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD2004G contains two (2) isolated high voltage silicon switching diodes, manufactured by the epitaxial planar process, epoxy molded in an SOT-563 surface mount package. These devices are designed for applications requiring high voltage capability.

MARKING CODE: DG



| MAXIMUM RATINGS: (T _A =25°C) | SYMBOL | | UNITS |
|--|-----------------------------------|-------------|-------|
| Continuous Reverse Voltage | V_{R} | 240 | V |
| Peak Repetitive Reverse Voltage | V_{RRM} | 300 | V |
| Peak Repetitive Reverse Current | IO | 200 | mA |
| Continuous Forward Current | l _F | 225 | mA |
| Peak Repetitive Forward Current | I _{FRM} | 625 | mA |
| Peak Forward Surge Current, tp=1.0µs | I _{FSM} | 4.0 | Α |
| Peak Forward Surge Current, tp=1.0s | I _{FSM} | 1.0 | Α |
| Power Dissipation | P_{D} | 250 | mW |
| Operating and Storage Junction Temperature | T _J , T _{stg} | -65 to +150 | °C |
| Thermal Resistance | $\Theta_{\sf JA}$ | 500 | °C/W |

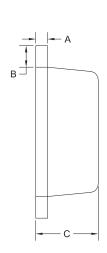
| ELECTRICAL | L CHARACTERISTICS PER DIODE | E: (T _A =25°C unless | otherwise noted) | |
|---------------------------------|--|---------------------------------|------------------|--------------------|
| SYMBOL I _R | TEST CONDITIONS V _R =240V | MIN | MAX 100 | UNITS nA |
| I_{R} | V _R =240V, T _A =150°C | | 100 | μΑ |
| BV_R | I _R =100μA | 300 | | V |
| V_{F} | I _F =100mA | | 1.0 | V |
| CJ | V _R =0, f=1.0MHz | | 5.0 | pF |
| t _{rr} | I _F =I _R =30mA, I _{rr} =3.0mA, R _L =1000 | Ω | 50 | ns |

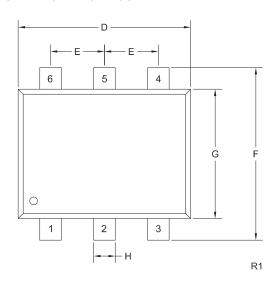
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SURFACE MOUNT SILICON **DUAL, ISOLATED** HIGH VOLTAGE **SWITCHING DIODE**

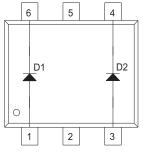


SOT-563 CASE - MECHANICAL OUTLINE





PIN CONFIGURATION



| DIMENSIONS | | | | | | |
|-------------------|--------|-------|-------------|------|--|--|
| | INCHES | | MILLIMETERS | | | |
| SYMBOL | MIN | MAX | MIN | MAX | | |
| Α | 0.0027 | 0.007 | 0.07 | 0.18 | | |
| В | 0.008 | | 0.20 | | | |
| С | 0.017 | 0.024 | 0.45 | 0.60 | | |
| D | 0.059 | 0.067 | 1.50 | 1.70 | | |
| E | 0.020 | | 0.50 | | | |
| F | 0.061 | 0.067 | 1.55 | 1.70 | | |
| G | 0.045 | 0.049 | 1.15 | 1.25 | | |
| Н | 0.006 | 0.012 | 0.15 | 0.30 | | |
| SOT-563 (REV: R1) | | | | | | |

LEAD CODE:

- 1) Anode D1 2) NC
- 3) Anode D2
- 4) Cathode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: DG

R1 (17-January 2014)